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**REVOCATION AND NEW POWER OF ATTORNEY AND
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

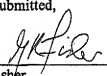
Customer Number: 76681

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)


MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property***, has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

ATTORNEY REFERENCE	CONF. NO	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2358.4	5661	US-2002-0043206 A1 4/18/2002	10/003,812	6,726,764 4/27/2004	MEMC Electronic Materials, Inc.	Continuation of 09/495,563 recorded at 011300/0967	METHOD FOR CONTROLLING GROWTH OF A SILICON CRYSTAL TO MINIMIZE GROWTH RATE AND DIAMETER DEVIATIONS
MEMC2358.5	6659		09/287,916	6,241,818 8/5/2001	MEMC Electronic Materials, Inc.	00992/4003-30	METHOD AND SYSTEM OF CONTROLLING TAPER GROWTH IN A SEMICONDUCTOR CRYSTAL GROWTH PROCESS
MEMC2395	9222		09/268,988 3/16/1999	6,214,109 4/10/2001	MEMC Electronic Materials, Inc.	Division of 08/792,527 recorded at 00338/00758	APPARATUS FOR CONTROLLING THE OXYGEN CONTENT IN SILICON WAFERS HEAVILY DOPED WITH ANTIMONY OR ARSENIC
MEMC2410	2418		09/270,366 3/18/1999	6,376,842 4/30/2002	MEMC Electronic Materials, Inc.	01028/70032	VACANCY DOMINATED, DEFECT-FREE SILICON
MEMC2410.1	8344	US 2002-0078880-A1 6/27/2002	10/000,545 10/24/2001	6,840,957 1/11/2005	MEMC Electronic Materials, Inc.	Division of 09/270,366 recorded at 01028/70032	VACANCY DOMINATED, DEFECT-FREE SILICON
28744-251 (MEMC2410.3)	7713	US2005-0238905 A1 10/27/2005	11/02,241 4/8/2005		MEMC Electronic Materials, Inc.	Continuation of 10/189,138 which is a continuation of 10/000,545 recorded at 01028/70032	VACANCY-DOMINATED, DEFECT-FREE SILICON
MEMC2442.1	1383		09/861,522 9/14/2000	6,391,682 5/27/2002	MEMC Electronic Materials, Inc.	011289/0576	PROCESS FOR DETECTING AGGLOMERATED INTRINSIC POINT DEFECTS BY METAL DECORATION
MEMC2443.1	1384		09/881,182 9/14/2000	6,535,537 10/21/2003	MEMC Electronic Materials, Inc.	011316/0129	METHOD FOR PRODUCING C200H0.8X1 SILICON FREE OF AGGLOMERATED SELF-INTERSTITIAL DEFECTS
28744-72 (MEMC2444.8)	4026	US2008-0196537 A1 10/22/2003	10/430,483 5/6/2003		MEMC Electronic Materials, Inc.	Continuation of 09/881,182 recorded at 011332/0536	PROCESS FOR SUPPRESSING THE NUCLEATION AND/OR GROWTH OF INTERSTITIAL TYPE DEFECTS BY CONTROLLING THE COOLING RATE THROUGH SILICON LEAKAGE
MEMC2443.2	7412		09/807,907 6/8/2001	6,520,181 2/18/2003	MEMC Electronic Materials, Inc.	011697/0310	CARRIER FOR CLEANING SILICON WAFERS
MEMC2458	8592	US 2007-0063268-A1 6/14/2001	09/344,036 5/23/1999	6,312,516 1/16/2001	MEMC Electronic Materials, Inc.	0103461/0004	PROCESS FOR PREPARING DEFECT-FREE SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN PROCESS CONDITIONS
MEMC2468.1	7075	US-2001-0027743-A1 10/11/2001	09/953,282 5/11/2001	6,500,255 12/31/2002	MEMC Electronic Materials, Inc.	Continuation of 09/344,036 recorded at 010463/0004	PROCESS FOR GROWING SILICON CRYSTALS WHICH ALLOWS FOR VARIABILITY IN THE PROCESS CONDITIONS WHILE SUPPRESSING THE FORMATION OF AGGLOMERATED INTRINSIC POINT DEFECTS